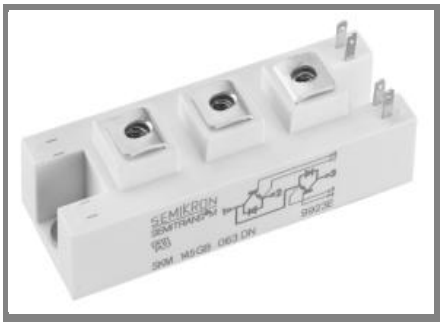
SKM 195GB126DN



SEMITRANS™ 2N

Trench IGBT Module

SKM 195GB126DN

SKM 195GAL126DN

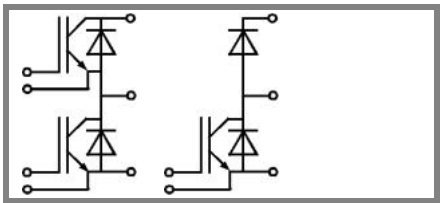
Preliminary Data

Features

- Homogeneous Si
- Trench = Trenchgate technology
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, self limiting to 6 x I_c

Typical Applications

- AC inverter drives
- UPS
- Electonic welders



GB GAL

Absolute Maximum Ratings		T_c = 25 °C, unless otherwise specified	
Symbol	**Conditions**	**Values**	**Units**
IGBT			
V_{CES}		1200	V
I_C	T_c = 25 (80) °C	220 (160)	A
I_{CRM}	t_p = 1 ms	300	A
V_{GES}		± 20	V
T_{vj}, (T_{stg})	$T_{OPERATION} \leq T_{stg}$	- 40 ... + 150 (125)	°C
V_{isol}	AC, 1 min.	4000	V
Inverse diode			
I_F	T_c = 25 (80) °C	200 (160)	A
I_{FRM}	t_p = 1 ms	300	A
I_{FSM}	t_p = 10 ms; sin.; T_j = 150 °C	1450	A
Freewheeling diode			
I_F	T_c = 25 (80) °C	200 (160)	A
I_{FRM}	T_c = 25 (80) °C, t_p = 1 ms	440 (320)	A
I_{FSM}	t_p = 10 ms; sin.; T_j = 150 °C	1450	A

Characteristics		T_c = 25 °C, unless otherwise specified			
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
IGBT					
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 6 mA	5	5,8	6,5	V
I_{CES}	V_{GE} = 0, V_{CE} = V_{CES}, T_j = 25 (125) °C		0,2	0,6	mA
$V_{CE(TO)}$	T_j = 25 (125) °C		1 (0,9)	1,15	V
r_{CE}	V_{GE} = 15 V, T_j = 25 (125) °C		4,7 (7,3)	6,7	mΩ
$V_{CE(sat)}$	I_C = 150 A, V_{GE} = 15 V, chip level		1,7 (2)	2,15	V
C_{ies}	under following conditions		10,5		nF
C_{oes}	V_{GE} = 0, V_{CE} = 25 V, f = 1 MHz		0,9		nF
C_{res}			0,8		nF
L_{CE}				25	nH
$R_{CC'+EE'}$	res., terminal-chip T_c= 25 (125) °C		0,75 (1)		mΩ
$t_{d(on)}$	V_{CC} = 600 V, I_C = 150 A		300		ns
t_r	R_{Gon} = R_{Goff} = 5 Ω, T_j = 125 °C		40		ns
$t_{d(off)}$	V_{GE} = ± 15 V		560		ns
t_f			100		ns
E_{on} (E_{off})			16 (21)		mJ
Inverse diode					
V_F = V_{EC}	I_F = 150 A; V_{GE} = 0 V; T_j = 25 (125) °C		1,6 (1,6)	1,8 (1,8)	V
$V_{(TO)}$	T_j = 25 (125) °C		1 (0,8)	1,1 (0,9)	V
r_T	T_j = 25 (125) °C		4 (5,3)	4,7 (6)	mΩ
I_{RRM}	I_F = 150 A; T_j = 125 ( ) °C		200		A
Q_{rr}	di/dt = 2000 A/µs		33		µC
E_{rr}	V_{GE} = 0 V		14,5		mJ
FWD					
V_F = V_{EC}	I_F = 150 A; V_{GE} = 0 V, T_j = 25 (125) °C		1,6 (1,6)	1,8 (1,8)	V
$V_{(TO)}$	T_j = 25 (125) °C		1 (0,8)	1,1 (0,9)	V
r_T	T_j = 25 (125) °C		4 (5,3)	4,7 (6)	mΩ
I_{RRM}	I_F = 150 A; T_j = 125 ( ) °C		200		A
Q_{rr}	di/dt = 2000 A/µs		33		µC
E_{rr}	V_{GE} = 0 V		14,5		mJ
Thermal characteristics					
$R_{th(j-c)}$	per IGBT			0,16	K/W
$R_{th(j-c)D}$	per Inverse Diode			0,32	K/W
$R_{th(j-c)FD}$	per FWD			0,32	K/W
$R_{th(c-s)}$	per module			0,05	K/W
Mechanical data					
M_s	to heatsink M6	3		5	Nm
M_t	to terminals M5	2,5		5	Nm
w				160	g

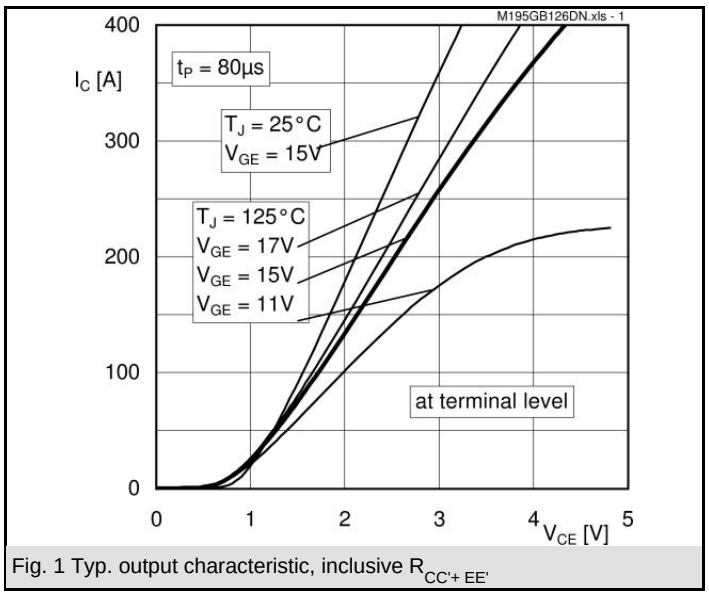


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

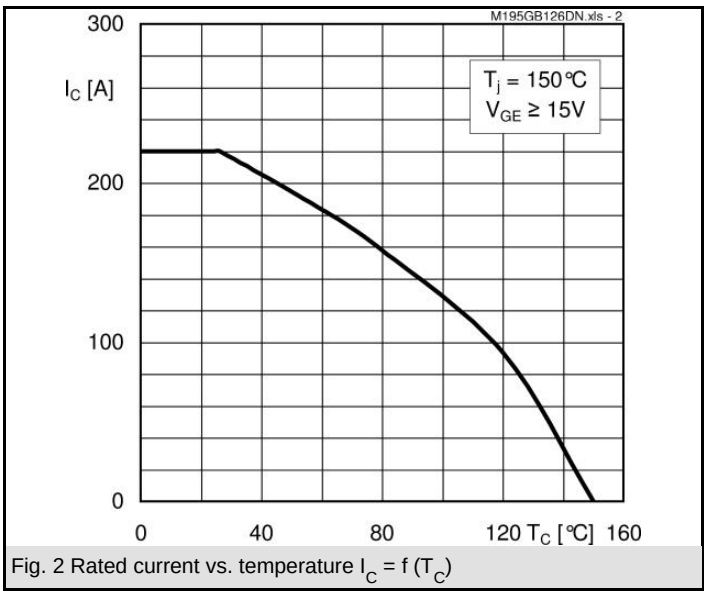


Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

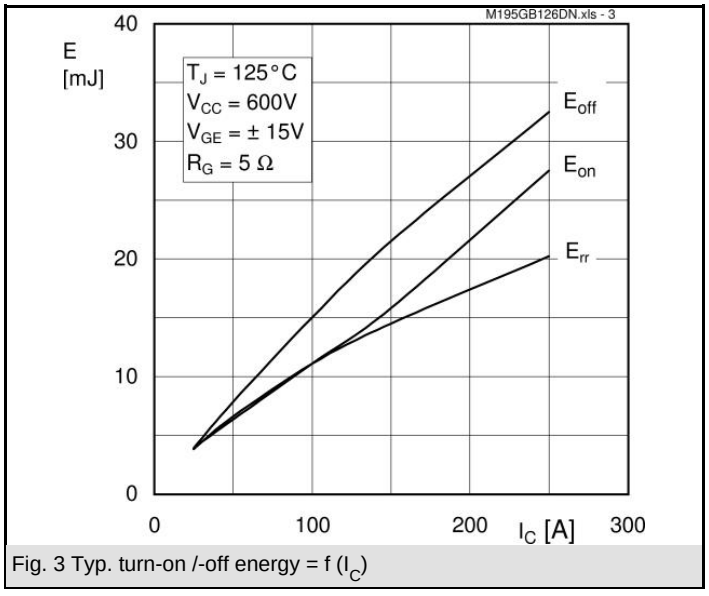


Fig. 3 Typ. turn-on /-off energy = f (I_C)

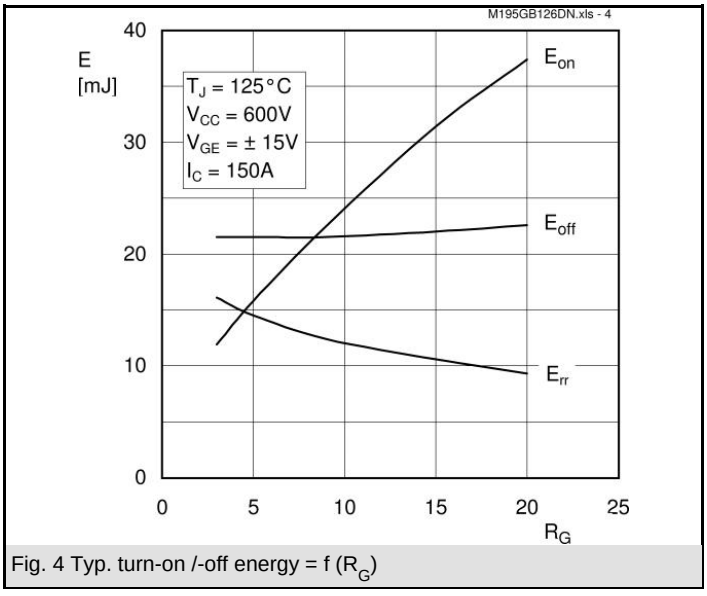


Fig. 4 Typ. turn-on /-off energy = f (R_G)

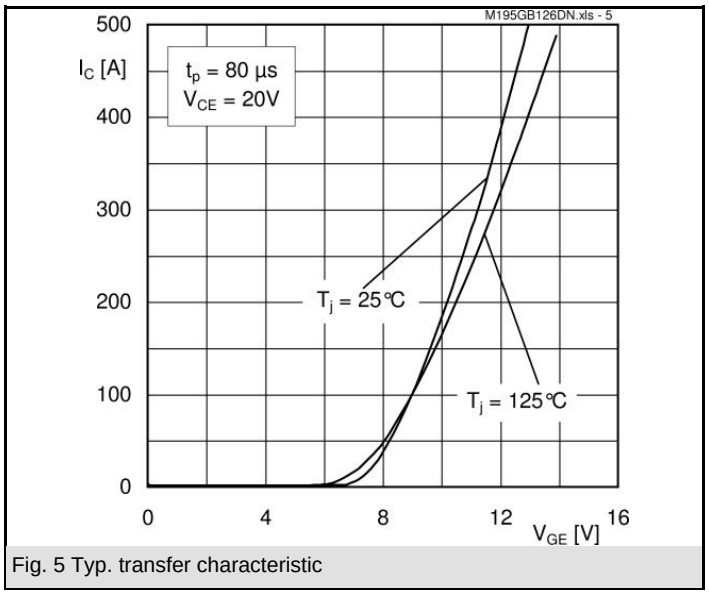


Fig. 5 Typ. transfer characteristic

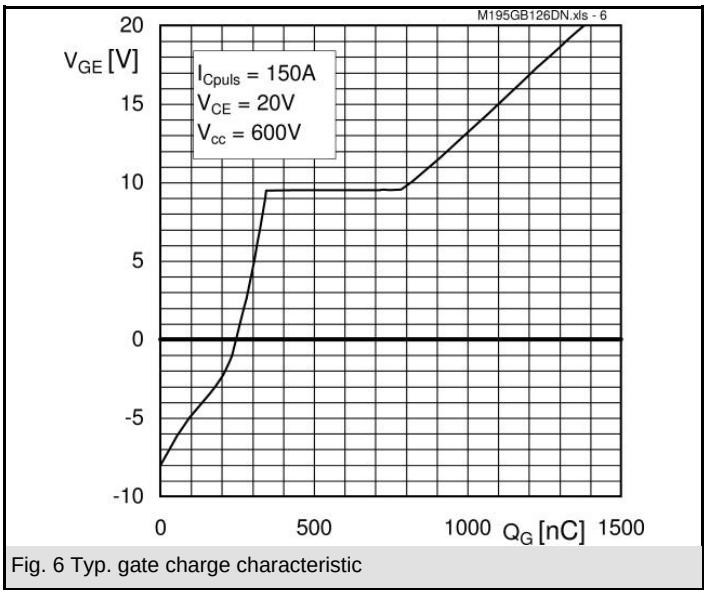


Fig. 6 Typ. gate charge characteristic

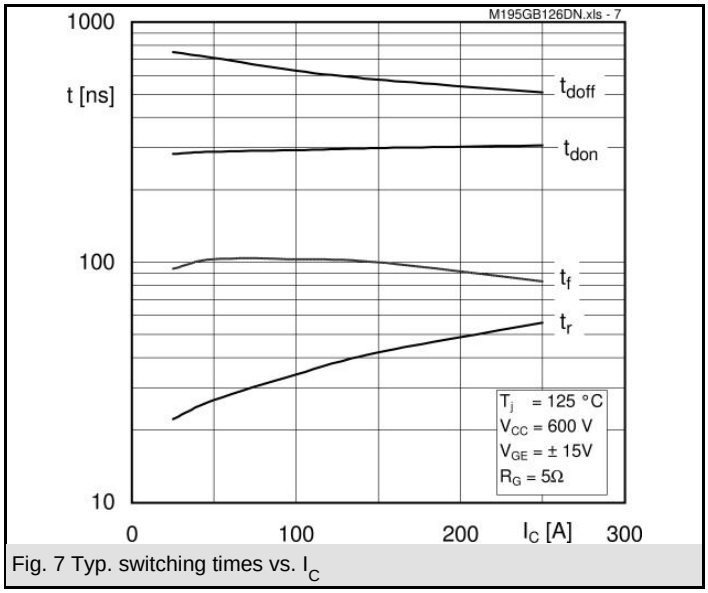


Fig. 7 Typ. switching times vs. I_C

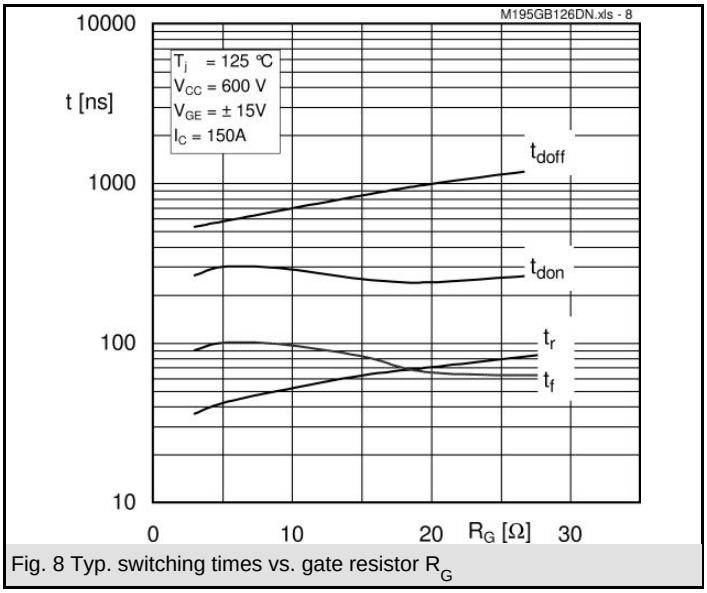


Fig. 8 Typ. switching times vs. gate resistor R_G

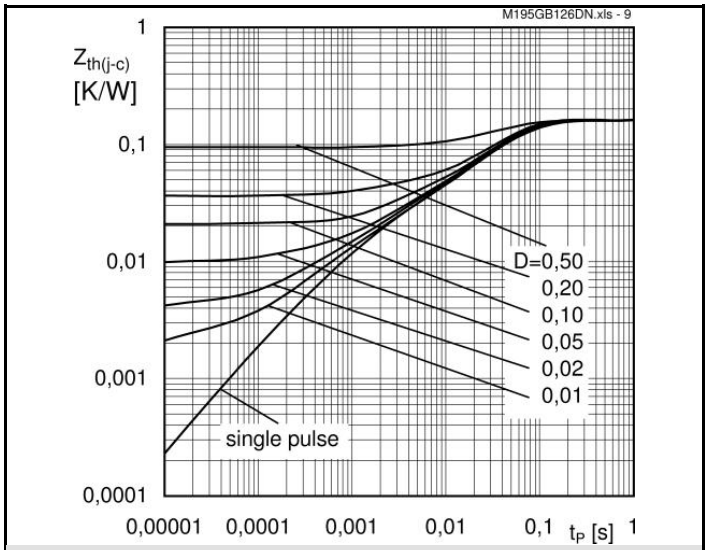


Fig. 9 Transient thermal impedance of IGBT

$Z_{thp(j-c)} = f(t_p)$; $D = t_p/t_c = t_p * f$

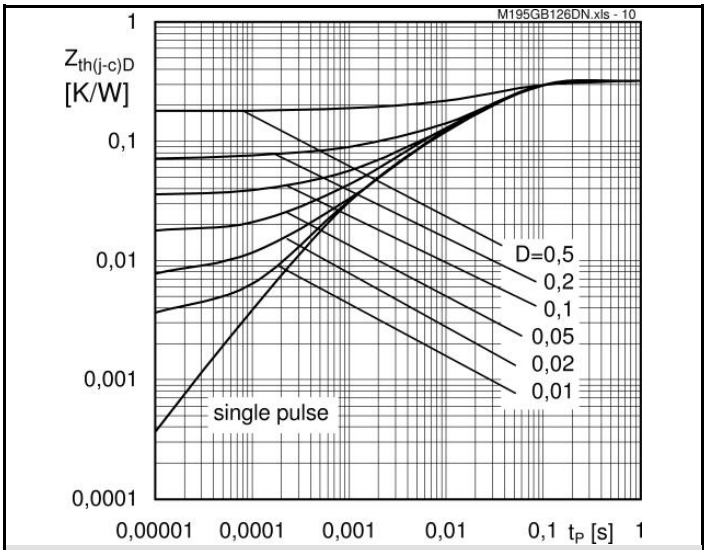


Fig. 10 Transient thermal impedance of FWD

$Z_{thp(j-c)} = f(t_p)$; $D = t_p/t_c = t_p * f$

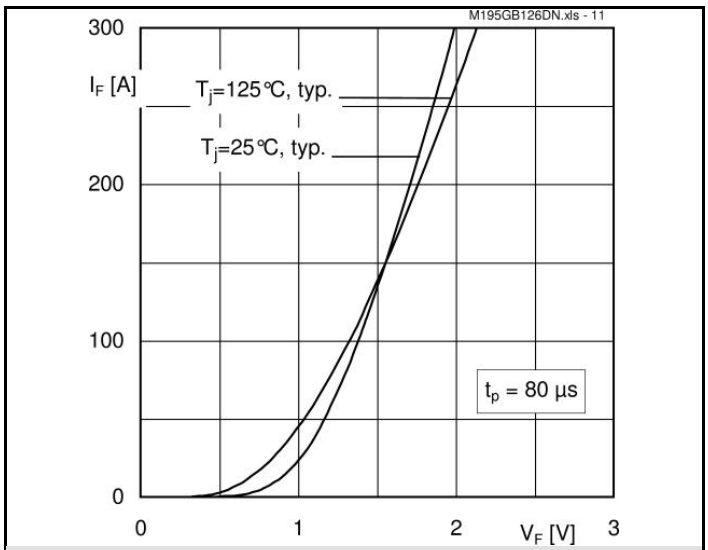


Fig. 11 CAL diode forward characteristic

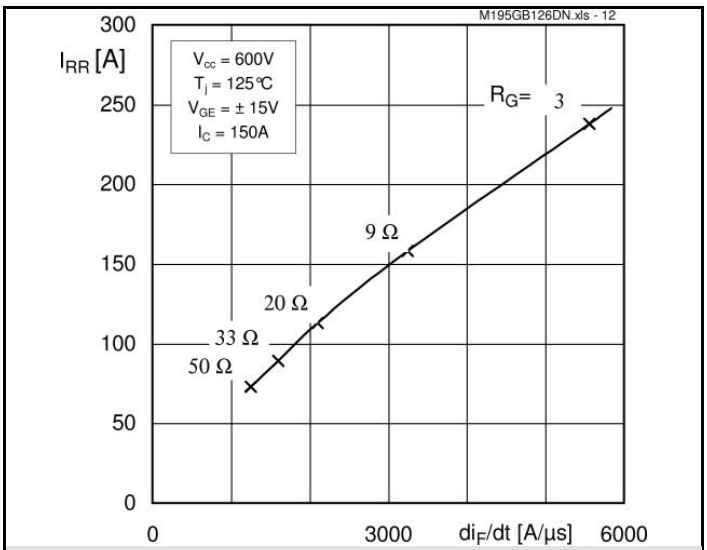


Fig. 12 Typ. CAL diode peak reverse recovery current

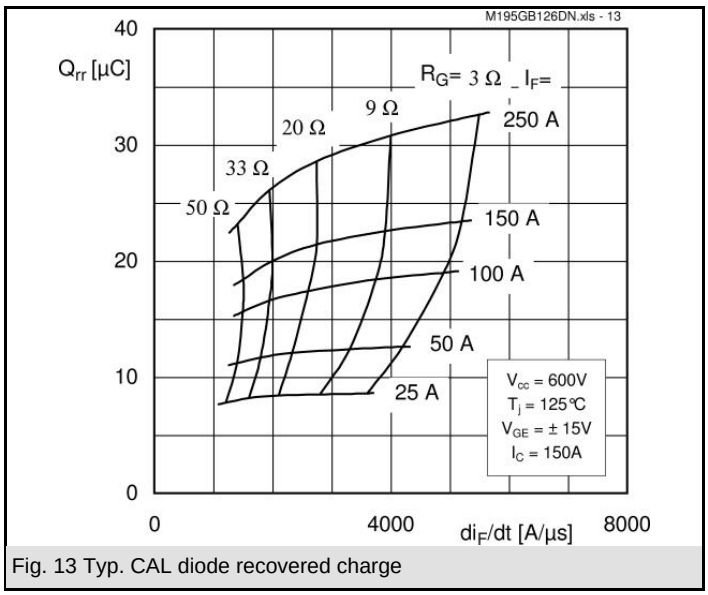
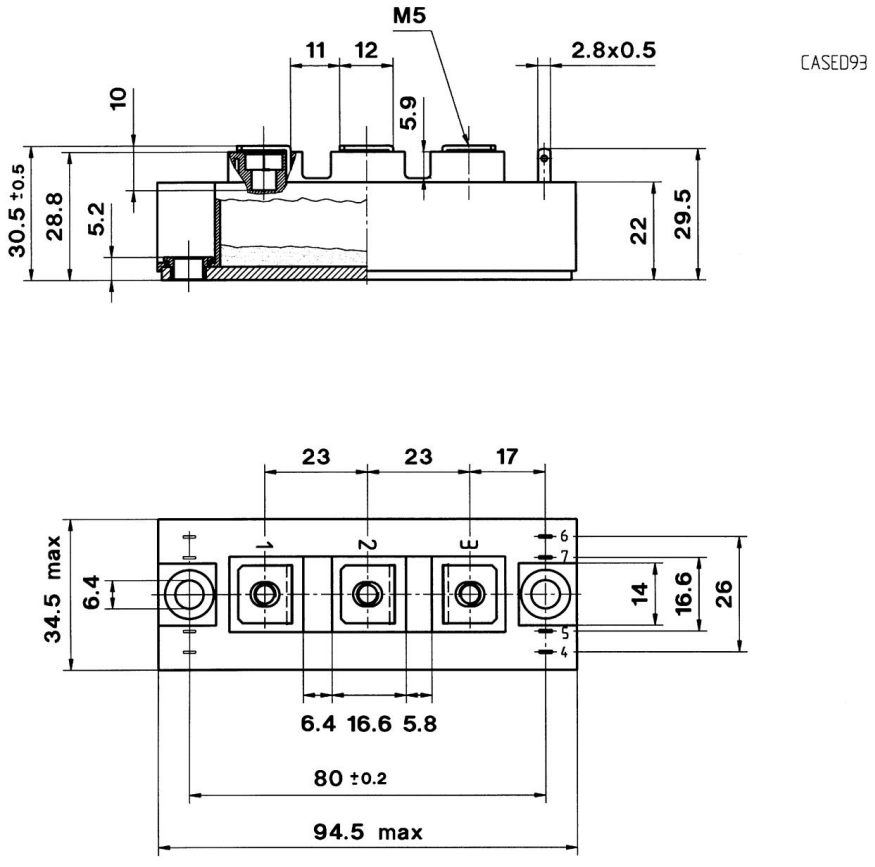


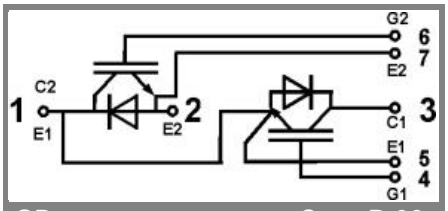
Fig. 13 Typ. CAL diode recovered charge

UL Recognized
File no. E 63 532

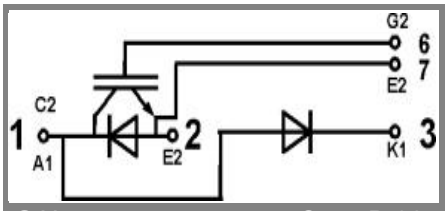
Dimensions in mm



Case D 93



GB Case D 93



GAL Case D 93

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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